

TM02N02I

N-Channel Enhancement Mosfet

General Description

- Low $R_{DS(ON)}$
- RoHS and Halogen-Free Compliant

Applications

- Load switch
- PWM

Product Summary

$V_{DS} = 20V$ $I_D = 2.3A$

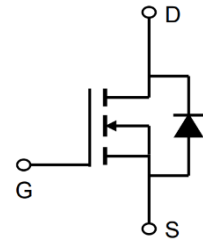
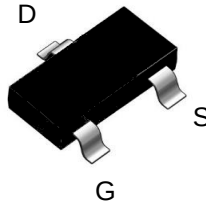
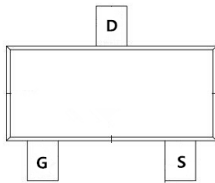
$R_{DS(ON)} = 50\text{ m}\Omega$ (typ.) @ $V_{GS} = 4.5V$

100% UIS Tested

100% R_g Tested



I: SOT-23



Marking: A2SHB OR A09T

Absolute Maximum Ratings ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 10	V
$I_D @ T_A = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	2.3	A
$I_D @ T_A = 70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	0.95	A
I_{DM}	Pulsed Drain Current ²	8	A
$P_D @ T_A = 25^\circ\text{C}$	Total Power Dissipation ³	0.85	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	162	$^\circ\text{C/W}$
R	Thermal Resistance Junction Case ¹			$^\circ\text{C/W}$

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Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V,I _D =250μA	20	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =20V, V _{GS} = 0V,	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V,V _{GS} = ±12V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D =250μA	0.4	0.7	1.0	V
R _{DS(on)}	Static Drain-Source on-Resistance note2	V _{GS} =4.5V, I _D =3A	-	50	70	mΩ
		V _{GS} =2.5V, I _D =2A	-	70	95	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =10V, V _{GS} =0V, f = 1.0MHz	-	124	-	pF
C _{oss}	Output Capacitance		-	28	-	pF
C _{rss}	Reverse Transfer Capacitance		-	25	-	pF
Q _g	Total Gate Charge	V _{DS} =10V, I _D =3A, V _{GS} =4.5V	-	2.7	-	nC
Q _{gs}	Gate-Source Charge		-	0.4	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	0.5	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DS} =10V,I _D =3A, R _{GEN} =3Ω, V _{GS} =4.5V	-	4	-	ns
t _r	Turn-on Rise Time		-	30	-	ns
t _{d(off)}	Turn-off Delay Time		-	10	-	ns
t _f	Turn-off Fall Time		-	3.5	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	2.3	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	10	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _S =3A	-	-	1.2	V

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

Typical Performance Characteristics

Figure 1: Output Characteristics

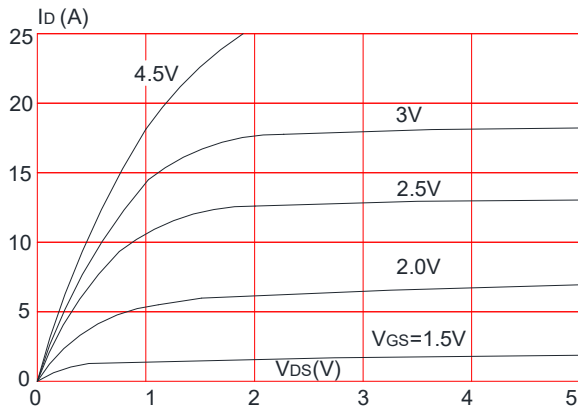


Figure 2: Typical Transfer Characteristics

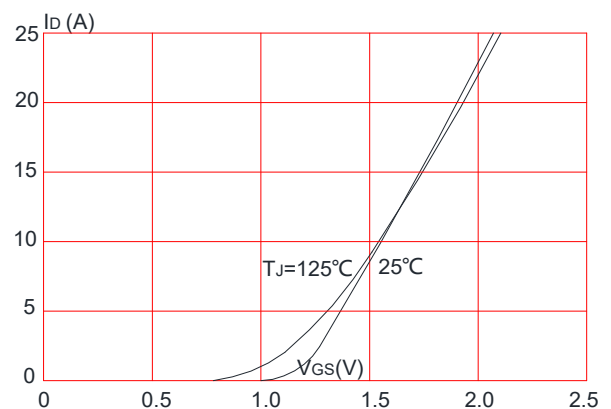


Figure 3: On-resistance vs. Drain Current

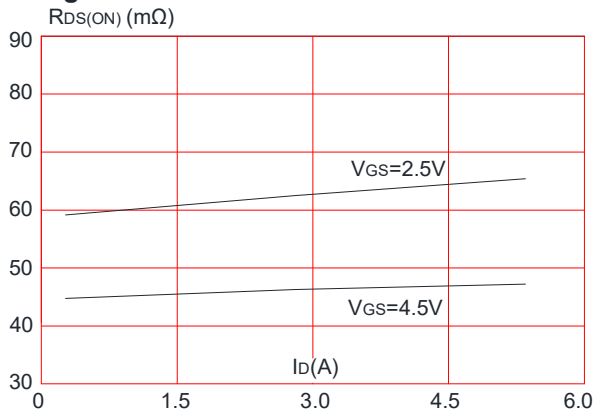


Figure 4: Body Diode Characteristics

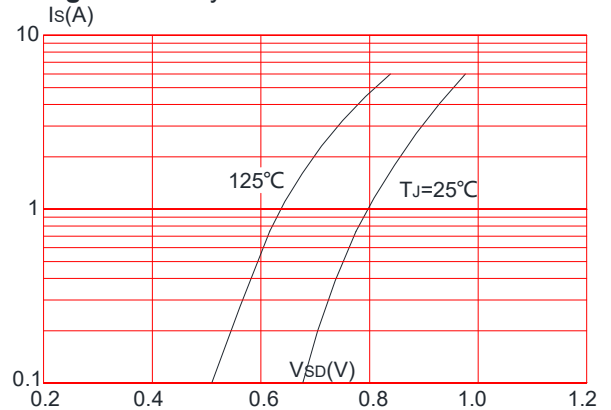


Figure 5: Gate Charge Characteristics

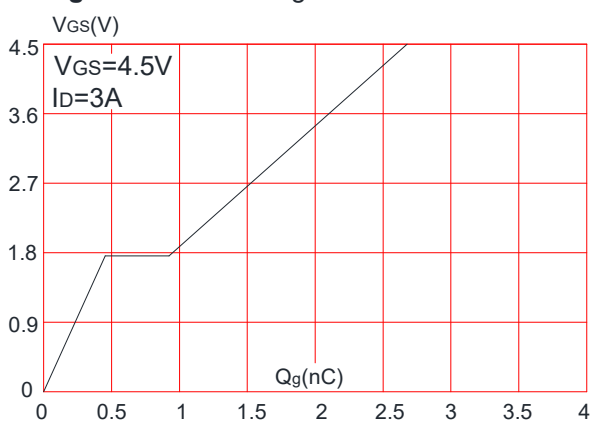
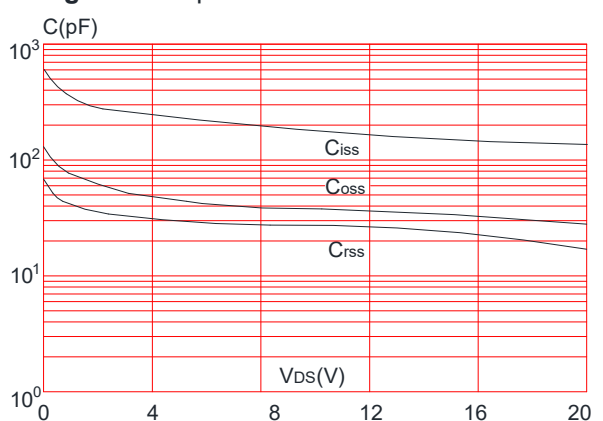


Figure 6: Capacitance Characteristics



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Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

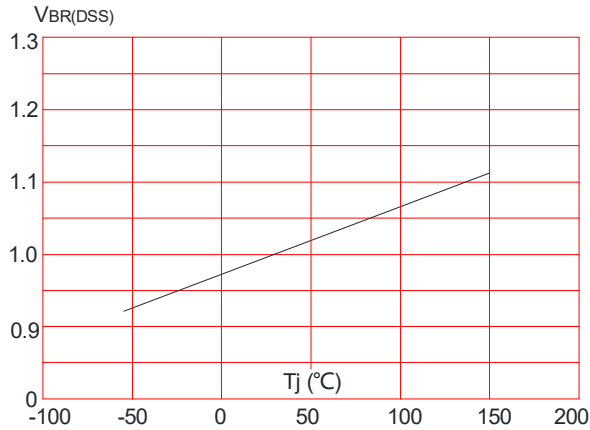


Figure 8: Normalized on Resistance vs. Junction Temperature

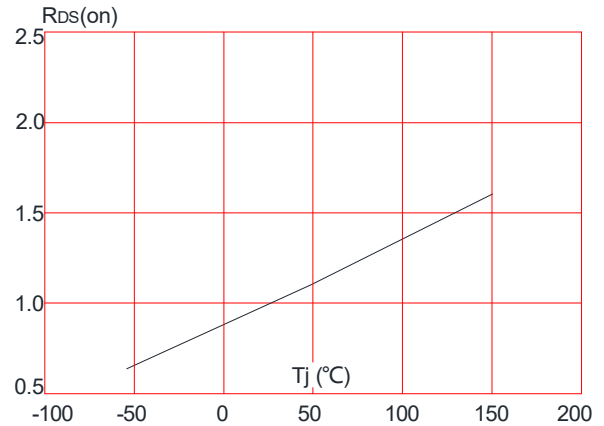


Figure 9: Maximum Safe Operating Area

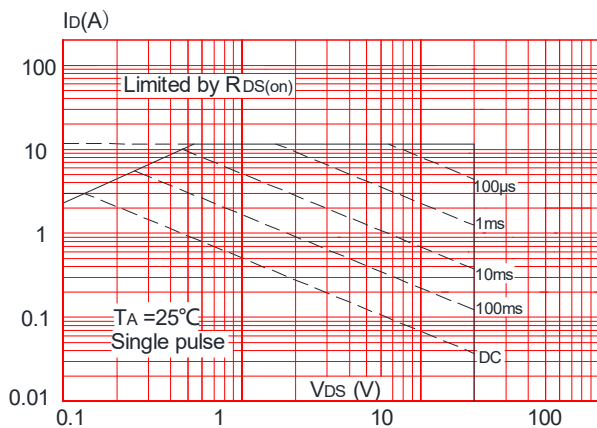


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

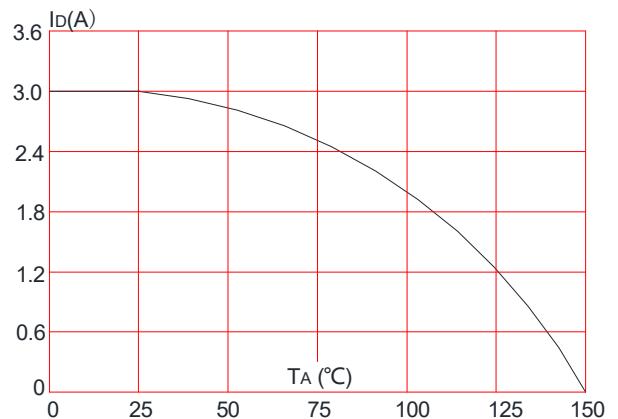
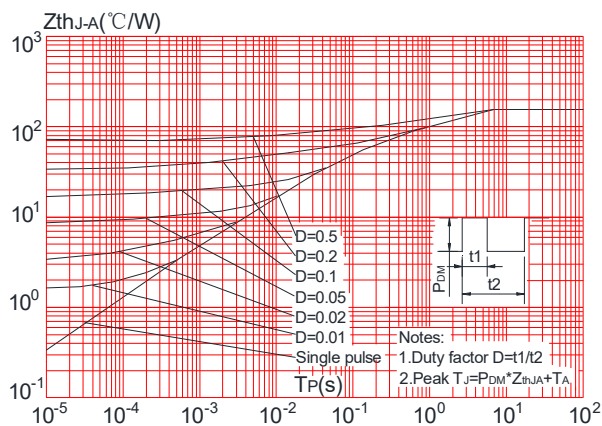
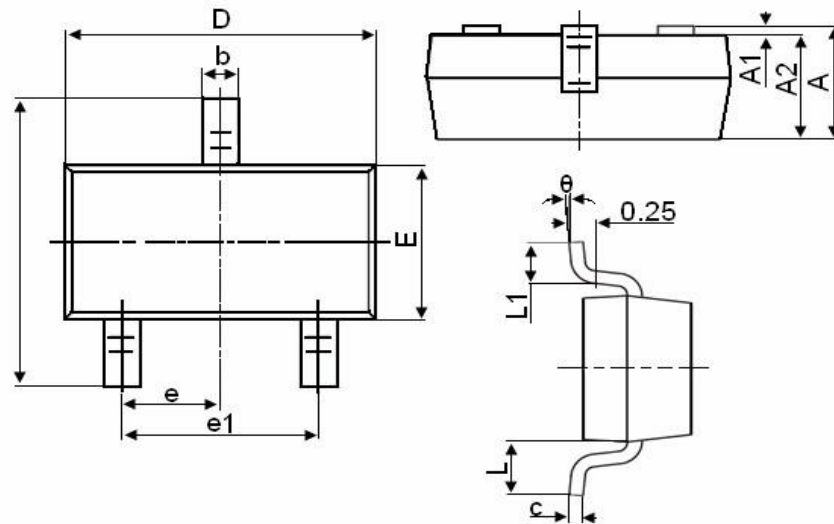


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



Package Mechanical Data: SOT-23



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°